

PROCEEDINGS OF SPIE

Novel In-Plane Semiconductor Lasers XIX

Alexey A. Belyanin
Peter M. Smowton
Editors

3–6 February 2020
San Francisco, California, United States

Sponsored and Published by
SPIE

Volume 11301

Proceedings of SPIE 0277-786X, V. 11301

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Novel In-Plane Semiconductor Lasers XIX, edited by Alexey A. Belyanin,
Peter M. Smowton, Proc. of SPIE Vol. 11301, 1130101 · © 2020 SPIE
CCC code: 0277-786X/20/\$21 · doi: 10.1117/12.2569981

Proc. of SPIE Vol. 11301 1130101-1

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Author(s), "Title of Paper," in *Novel In-Plane Semiconductor Lasers XIX*, edited by Alexey A. Belyanin, Peter M. Smowton, Proceedings of SPIE Vol. 11301 (SPIE, Bellingham, WA, 2020) Seven-digit Article CID Number.

ISSN: 0277-786X
ISSN: 1996-756X (electronic)

ISBN: 9781510633650
ISBN: 9781510633667 (electronic)

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445
SPIE.org

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